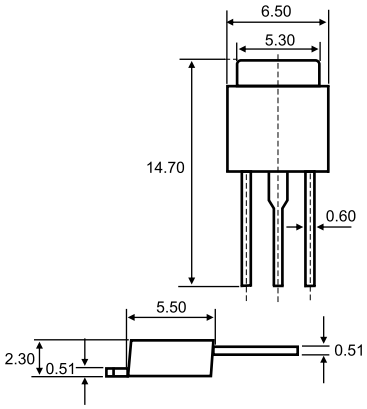
2SC4003(NPN)

TO-251/TO-252-2L Transistor

1. BASE
2. COLLECTOR
3. EMITTER

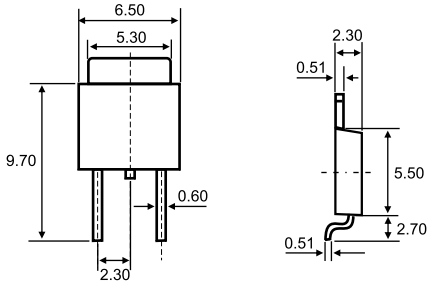
TO-251



Features

- ✧ **High h_{FE}** h_{FE}=60 to 200
- ✧ **low $V_{CE(sat)}$** $V_{CE(sat)}$=0.6V

TO-252-2L



Dimensions in inches and (millimeters)

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.2	A
P_C	Collector Power Dissipation	1	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA,I_E=0	400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=300V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=10V,I_C=50mA	60		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=50mA,I_B=5mA			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=50mA,I_B=5mA			1	V
Transition frequency	f_T	V_{CE}=30V,I_C=10mA		70		MHz

CLASSIFICATION OF h_{FE}

Rank	D	E
Range	60-120	100-200

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Typical Characteristics